

Product data sheet

## 1. Product profile

## 1.1 General description

NPN silicon planar epitaxial transistor in a 4-pin dual-emitter SOT343R plastic package.

### 1.2 Features and benefits

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability

## 1.3 Applications

- Intended for Radio Frequency (RF) front end applications in the GHz range, such as:
  - analog and digital cellular telephones
  - cordless telephones (Cordless Telephone (CT), Personal Communication Network (PCN), Digital Enhanced Cordless Telecommunications (DECT), etc.)
  - radar detectors
  - pagers
  - ◆ Satellite Antenna TeleVision (SATV) tuners

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{\text{CBO}}$	collector-base voltage	open emitter		-	-	15	V
$V_{CEO}$	collector-emitter voltage	open base		-	-	6	V
I <sub>C</sub>	collector current (DC)			-	-	10	mA
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 145  ^{\circ}C$	<u>[1]</u>	-	-	60	mW
h <sub>FE</sub>	DC current gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ $T_j = 25 \text{ °C}$		60	100	200	
$C_{CBS}$	collector-base capacitance	$V_{CB} = 5 \text{ V}; f = 1 \text{ MHz};$ emitter grounded		-	0.17	0.3	pF
f <sub>T</sub>	transition frequency	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ f = 1 GHz; $T_{amb} = 25 \text{ °C}$		-	14	-	GHz



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
MSG	maximum stable gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V};$ f = 1.8 GHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	18	-	dB
$ s_{21} ^2$	insertion power gain	$I_{C}$ = 5 mA; $V_{CE}$ = 3 V; f = 1.8 GHz; $T_{amb}$ = 25 °C; $Z_{S}$ = $Z_{L}$ = 50 $\Omega$	-	14	-	dB
NF	noise figure	$\Gamma_{\text{S}} = \Gamma_{\text{opt}}; \ I_{\text{C}} = 1 \text{ mA};$ $V_{\text{CE}} = 3 \text{ V}; \ f = 2 \text{ GHz}$	-	1	-	dB

<sup>[1]</sup>  $T_{sp}$  is the temperature at the soldering point of the collector pin.

# 2. Pinning information

Table 2. Pinning

	3	
Pin	Description	Simplified outline Symbol
1	collector	
2	emitter	3 4 1
3	base	3—
4	emitter	2,4
		2 1 sym086

# 3. Ordering information

Table 3. Ordering information

Type number	Package	Package			
	Name	Description	Version		
BFG310W/XR	-	plastic surface mounted package; reverse pinning; 4 leads	SOT343R		

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BFG310W/XR	A7*

<sup>[1] \* =</sup> p: made in Hong Kong.

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	15	V
$V_{CEO}$	collector-emitter voltage	open base	-	6	V
$V_{EBO}$	emitter-base voltage	open collector	-	2	V
I <sub>C</sub>	collector current (DC)		-	10	mA
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 145  ^{\circ}C$	<u>[1]</u> -	60	mW
T <sub>stg</sub>	storage temperature		-65	+175	°C
Tj	junction temperature		-	175	°C

<sup>[1]</sup>  $T_{sp}$  is the temperature at the soldering point of the collector pin.

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	$T_{sp} \le 145  ^{\circ}C$	<u>[1]</u> 530	K/W

<sup>[1]</sup>  $T_{sp}$  is the temperature at the soldering point of the collector pin.

## 7. Characteristics

Table 7. Characteristics

 $T_i = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$I_E = 0 A; V_{CB} = 6 V$	-	-	15	nΑ
h <sub>FE</sub>	DC current gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}$	60	100	200	
C <sub>CBS</sub>	collector-base capacitance	V <sub>CB</sub> = 5 V; f = 1 MHz; emitter grounded	-	0.17	0.3	pF
C <sub>CES</sub>	collector-emitter capacitance	V <sub>CE</sub> = 5 V; f = 1 MHz; base grounded	-	0.22	-	pF
C <sub>EBS</sub>	emitter-base capacitance	V <sub>EB</sub> = 0.5 V; f = 1 MHz; collector grounded	-	0.16	-	pF
f <sub>T</sub>	transition frequency	$I_C = 5$ mA; $V_{CE} = 3$ V; $f = 1$ GHz; $T_{amb} = 25$ °C	-	14	-	GHz
MSG	maximum stable gain	$I_C = 5 \text{ mA}; V_{CE} = 3 \text{ V}; f = 1.8 \text{ GHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	18	-	dB
$ s_{21} ^2$	insertion power gain	$I_C$ = 5 mA; $V_{CE}$ = 3 V; $T_{amb}$ = 25 °C; $Z_S$ = $Z_L$ = 50 $\Omega$				
		f = 1.8 GHz	-	14	-	dB
		f = 3 GHz	-	11	-	dB
NF	noise figure	$\Gamma_{\text{s}} = \Gamma_{\text{opt}}$ ; $I_{\text{C}} = 1$ mA; $V_{\text{CE}} = 3$ V; $f = 2$ GHz	-	1	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	$I_C$ = 5 mA; $V_{CE}$ = 3 V; f = 1.8 GHz; $T_{amb}$ = 25 °C; $Z_S$ = $Z_L$ = 50 $\Omega$	-	1.8	-	dBm
IP3	third order intercept point	$I_C$ = 5 mA; $V_{CE}$ = 3 V; f = 1.8 GHz; $T_{amb}$ = 25 °C; $Z_S$ = $Z_L$ = 50 $\Omega$	-	8.5	-	dBm

BFG310W\_XR

**Product data sheet** 

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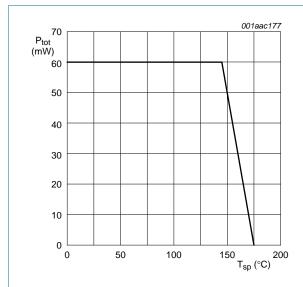


Fig 1. Power derating curve

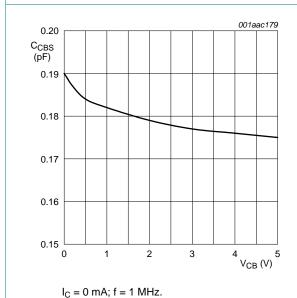


Fig 3. Collector-base capacitance as a function of collector-base voltage; typical values

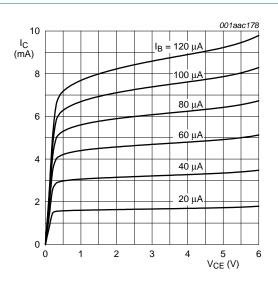
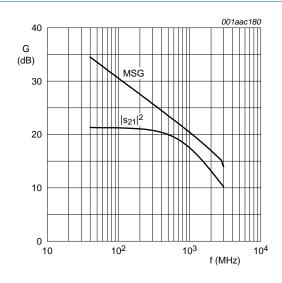


Fig 2. Collector current as a function of collector-emitter voltage; typical values



 $I_C = 5$  mA;  $V_{CE} = 3$  V.

Fig 4. Gain as a function of frequency; typical values

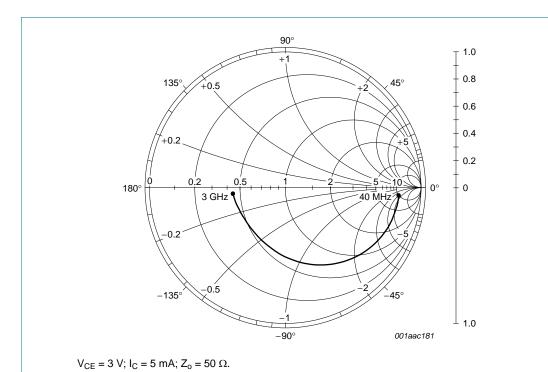


Fig 5. Common emitter input reflection coefficient (s<sub>11</sub>); typical values

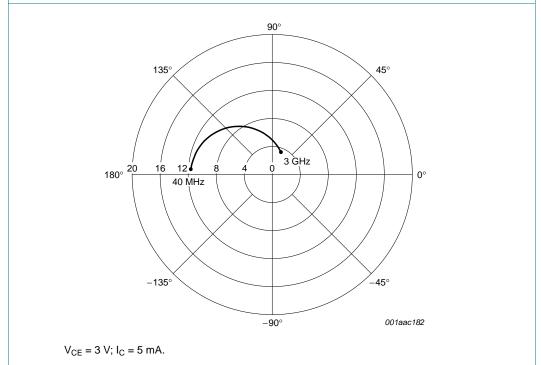


Fig 6. Common emitter forward transmission coefficient (s<sub>21</sub>); typical values

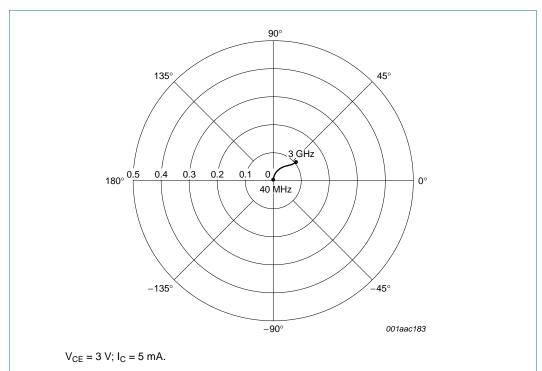


Fig 7. Common emitter reverse transmission coefficient (s<sub>12</sub>); typical values

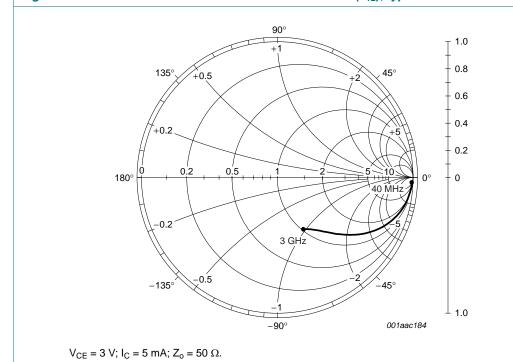


Fig 8. Common emitter output reflection coefficient (s<sub>22</sub>); typical values

# 8. Application information

Table 8. SPICE parameters of the BFG310W DIE

Sequence	Parameter	Value	Unit
1	IS	16.17	аА
2	BF	210	-
3	NF	1	-
4	VAF	50	V
5	IKF	59.83	mA
6	ISE	1.726	fA
7	NE	2.114	-
8	BR	6	-
9	NR	1	-
10	VAR	2.3	V
11	IKR	10	A
12	ISC	0	аА
13	NC	1.5	-
14	RB	3.6	Ω
15	RE	2.1	Ω
16	RC	1.6	Ω
17	CJE	115.6	fF
18	VJE	866.3	mV
19	MJE	0.285	-
20	CJC	68.18	fF
21	VJC	601	mV
22	MJC	0.123	-
23	XCJC	1	-
24	FC	0.7	-
25	TF	8.3	ps
26	XTF	10	-
27	VTF	1000	V
28	ITF	150	mA
29	PTF	0	deg
30	TR	0	ns
31	KF	0	-
32	AF	1	-
33	TNOM	25	°C
34	EG	1.014	eV
35	XTB	0	-
36	XTI	8	-
37	Q1.AREA	1	-

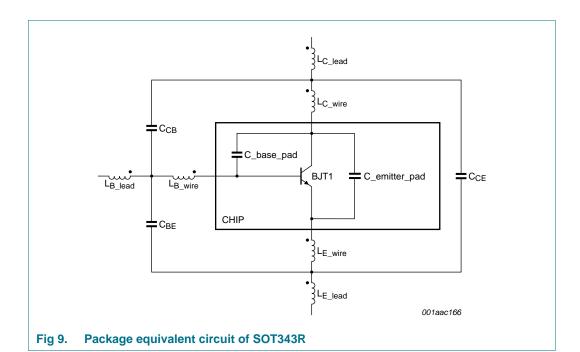


Table 9. List of components; see Figure 9

Designation	Value	Unit
$C_{CB}$	2	fF
C <sub>BE</sub>	80	fF
C <sub>CE</sub>	80	fF
C_base_pad	67	fF
C_emitter_pad	142	fF
L <sub>C_wire</sub>	0.767	nH
L <sub>B_wire</sub>	0.842	nH
L <sub>E_wire</sub>	0.212	nH
L <sub>C_lead</sub>	0.28	nH
L <sub>B_lead</sub>	0.281	nH
L <sub>E_lead</sub>	0.1	nH

## 9. Package outline

### Plastic surface-mounted package; reverse pinning; 4 leads

SOT343R

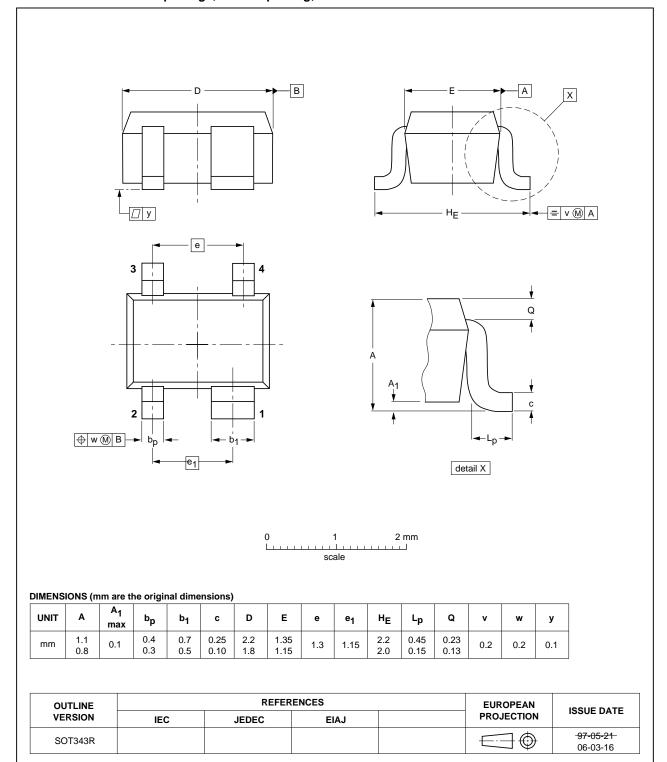


Fig 10. Package outline SOT343R

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# 10. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFG310W_XR v.2	20110915	Product data sheet	-	BFG310W_XR v.1
<ul> <li>Modifications:</li> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Package outline drawings have been updated to the latest version.</li> </ul>				re appropriate.
BFG310W_XR v.1 (9397 750 14245)	20050202	Product data sheet	-	-

## 11. Legal information

### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# BFG310W/XR

### **NPN 14 GHz wideband transistor**

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